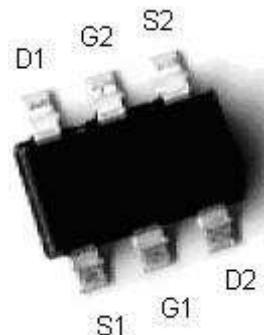


## N-CHANNEL MOSFET (dual transistors)

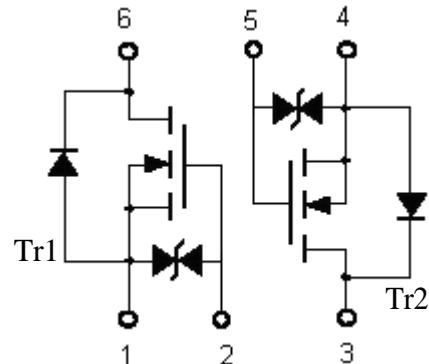
### Features:

- Low on-resistance
- High ESD capability
- High speed switching
- Low-voltage drive(1.8V)
- Pb-free lead plating and halogen-free package



SOT-363

BV <sub>DSS</sub>	20V
I <sub>D</sub> @V <sub>GS</sub> =4.5V, T <sub>A</sub> =25°C	760mA
R <sub>DSON</sub> @V <sub>GS</sub> =4.5V, I <sub>D</sub> =600mA	370mΩ (typ)
R <sub>DSON</sub> @V <sub>GS</sub> =2.5V, I <sub>D</sub> =400mA	500mΩ (typ)
R <sub>DSON</sub> @V <sub>GS</sub> =1.8V, I <sub>D</sub> =350mA	1.1Ω (typ)



**The following characteristics apply to both Tr1 and Tr2**

### Absolute Maximum Ratings (T<sub>a</sub>=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	
Continuous Drain Current @ T <sub>a</sub> =25°C, V <sub>GS</sub> =4.5V (Note 3)	I <sub>D</sub>	760	mA
Continuous Drain Current @ T <sub>a</sub> =85°C, V <sub>GS</sub> =4.5V (Note 3)		550	
Pulsed Drain Current (Notes 1, 2)	I <sub>DM</sub>	3	A
Maximum Power Dissipation (Note 3)	P <sub>D</sub>	300	mW
		160	
ESD susceptibility		2000 (Note 4)	V
Operating Junction and Storage Temperature	T <sub>j</sub> , T <sub>stg</sub>	-55~+150	°C

Note : 1. Pulse width limited by maximum junction temperature.

2. Pulse width≤ 300μs, duty cycle≤2%.

3.Surface mounted on 1 in<sup>2</sup>copper pad of FR-4 board, t≤5s.

4.Human body model, 1.5kΩ in series with 100pF



## Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient(PCB mounted) (Note)	R <sub>th,ja</sub>	417	°C/W

Note : Surface mounted on 1 in<sup>2</sup>copper pad of FR-4 board, t≤5s.

## Electrical Characteristics (T<sub>j</sub>=25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
B <sub>VDSS</sub>	20	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
ΔB <sub>VDSS</sub> /ΔT <sub>j</sub>	-	0.02	-	V/°C	Reference to 25°C, I <sub>D</sub> =1mA
V <sub>GS(th)</sub>	0.5	0.92	1.2	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
I <sub>GSS</sub>	-	-	±10	μA	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	1		V <sub>DS</sub> =20V, V <sub>GS</sub> =0V
	-	-	10		V <sub>DS</sub> =16V, V <sub>GS</sub> =0V (T <sub>j</sub> =70°C)
*R <sub>DSON</sub>	-	370	450	mΩ	V <sub>GS</sub> =4.5V, I <sub>D</sub> =600mA
	-	500	650		V <sub>GS</sub> =2.5V, I <sub>D</sub> =400mA
	-	1100	1300		V <sub>GS</sub> =1.8V, I <sub>D</sub> =350mA
*G <sub>FS</sub>	-	1.4	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =600mA
<b>Dynamic</b>					
C <sub>iss</sub>	-	60	-	pF	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz
C <sub>oss</sub>	-	14	-		
C <sub>rss</sub>	-	9	-		
t <sub>d(ON)</sub>	-	4	-	ns	V <sub>DS</sub> =10V, I <sub>D</sub> =600mA, V <sub>GS</sub> =10V R <sub>G</sub> =3.3Ω, R <sub>D</sub> =16.7Ω
t <sub>r</sub>	-	10	-		
t <sub>d(OFF)</sub>	-	15	-		
t <sub>f</sub>	-	2	-		
Q <sub>g</sub>	-	1.3	-	nC	V <sub>DS</sub> =16V, I <sub>D</sub> =600mA, V <sub>GS</sub> =4.5V
Q <sub>gs</sub>	-	0.3	-		
Q <sub>gd</sub>	-	0.5	-		
<b>Source-Drain Diode</b>					
*V <sub>SD</sub>	-	0.81	1.2	V	V <sub>GS</sub> =0V, I <sub>s</sub> =500mA

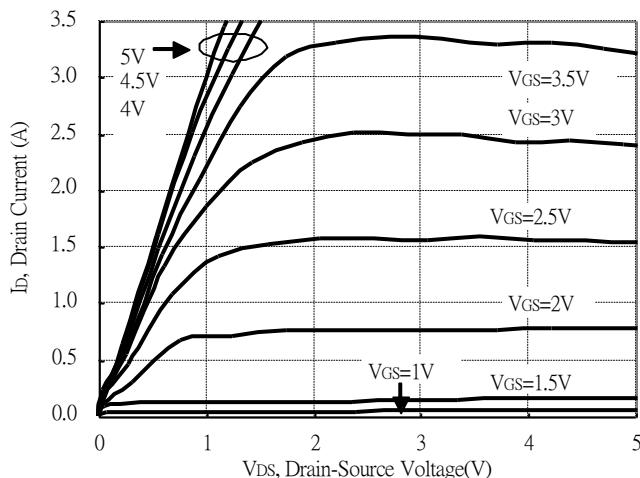
\*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

## Ordering Information

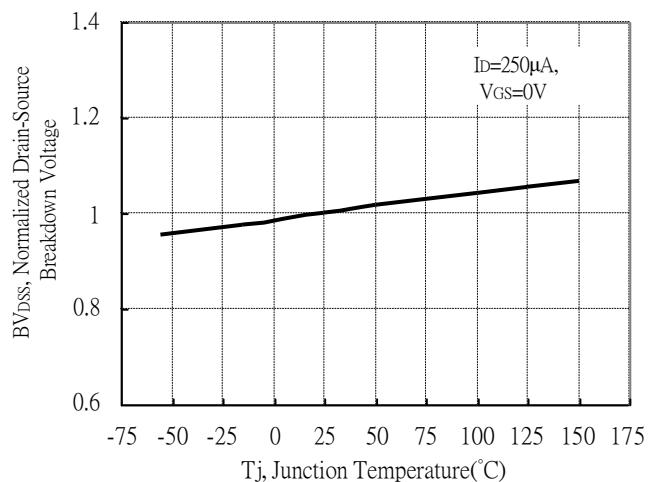
Device	Package	Shipping
KWDN6303S6R	SOT-363 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

## Typical Characteristics

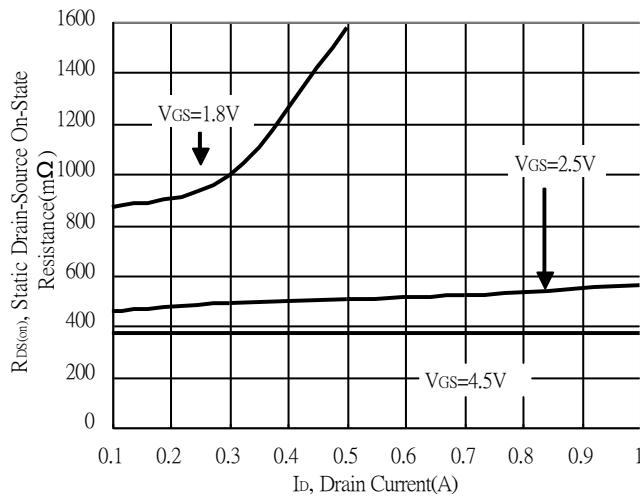
Typical Output Characteristics



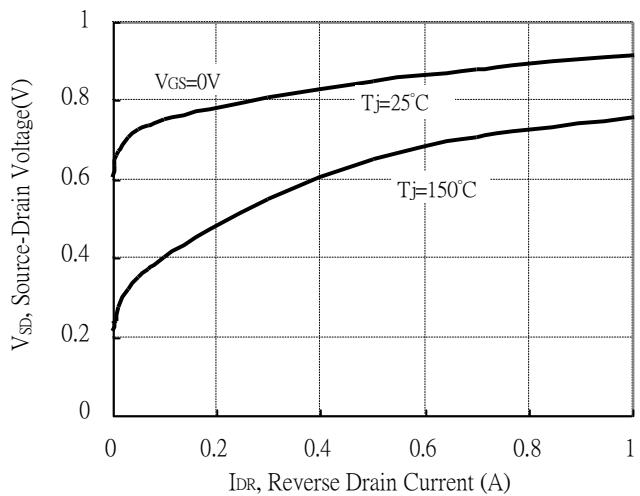
Breakdown Voltage vs Ambient Temperature



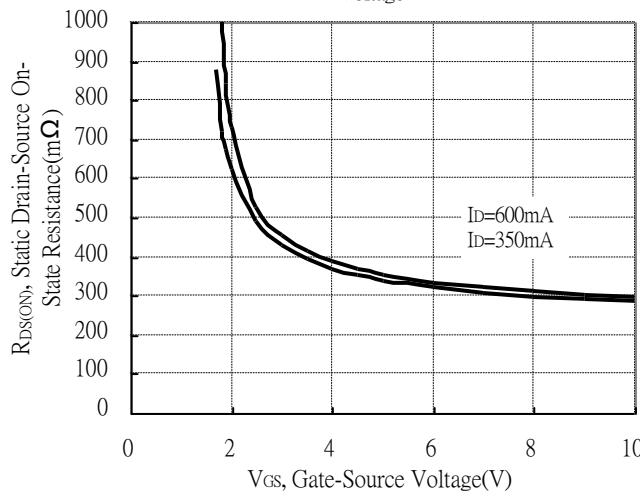
Static Drain-Source On-State resistance vs Drain Current



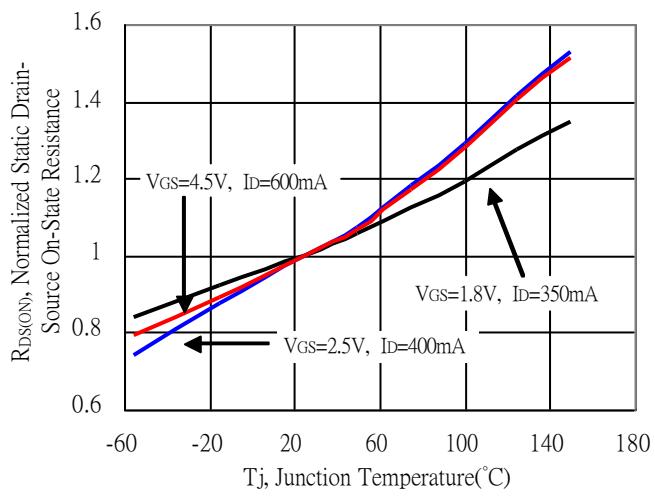
Reverse Drain Current vs Source-Drain Voltage



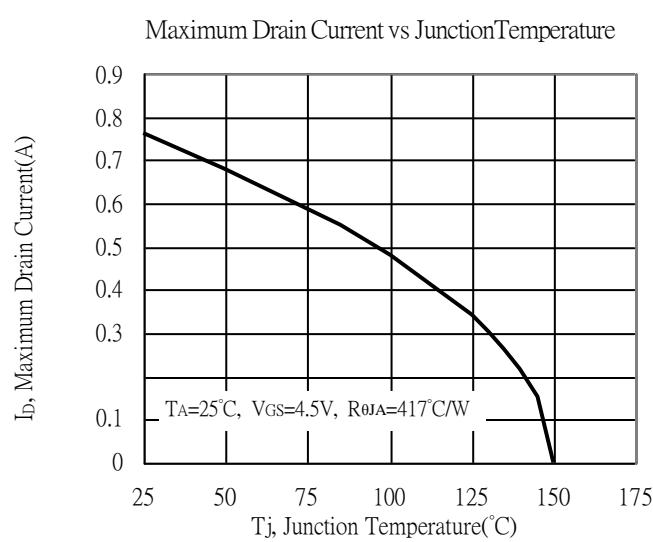
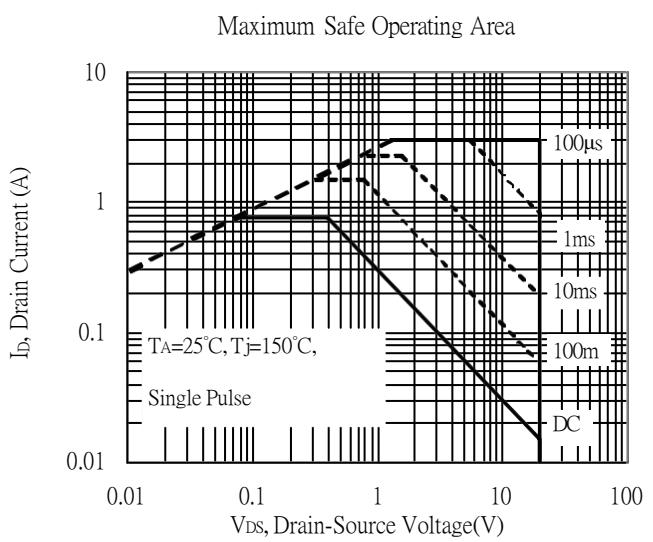
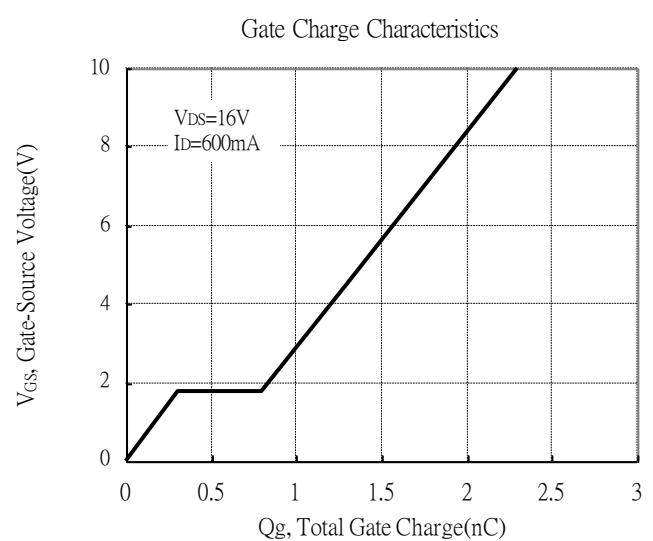
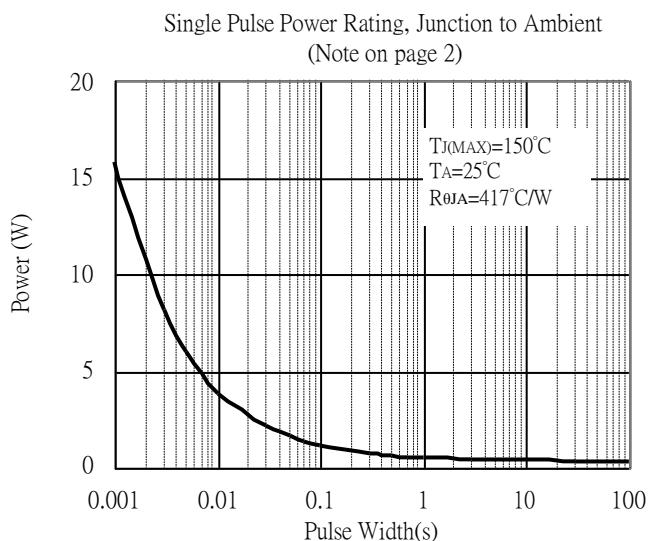
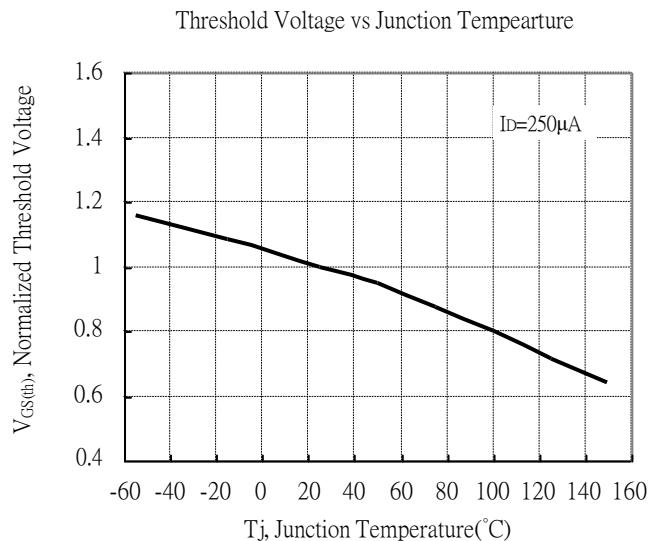
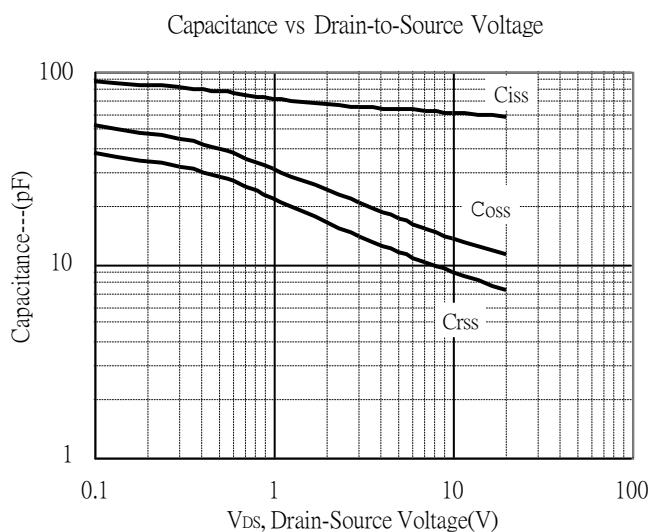
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Drain-Source On-State Resistance vs Junction Temperature

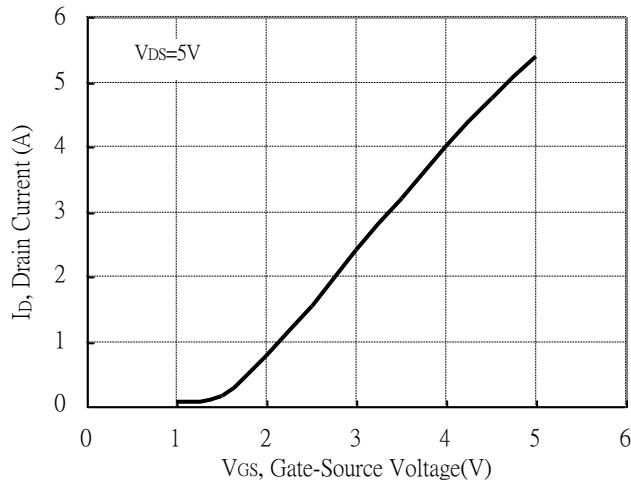


## Typical Characteristics(Cont.)

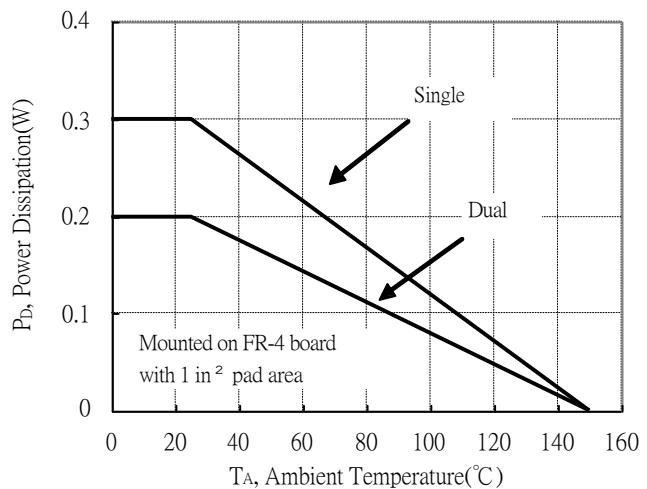


## Typical Characteristics(Cont.)

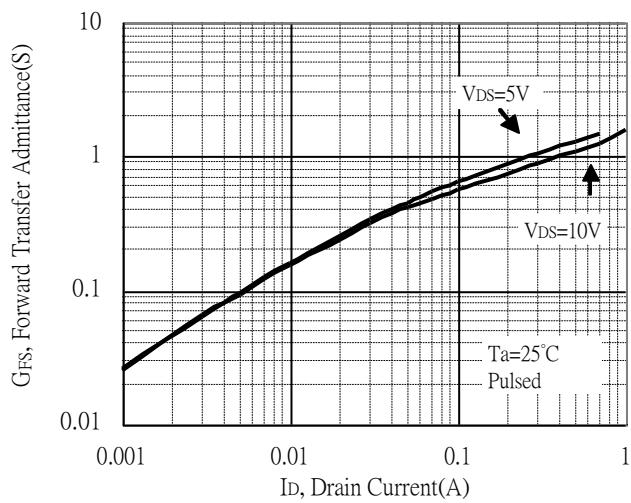
Typical Transfer Characteristics



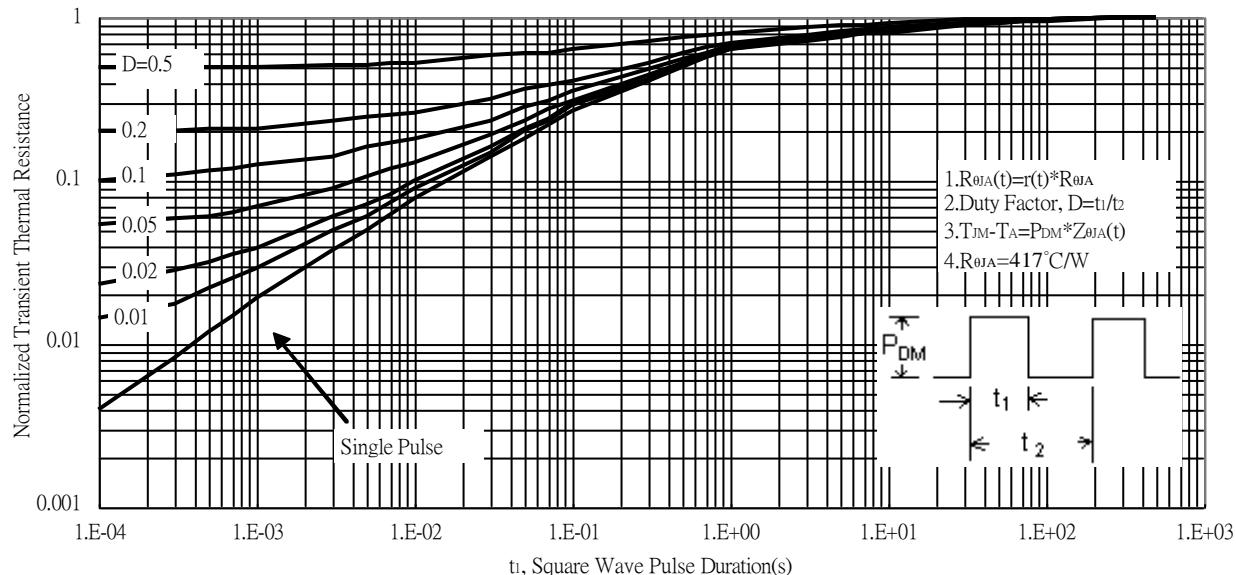
Power Derating Curve



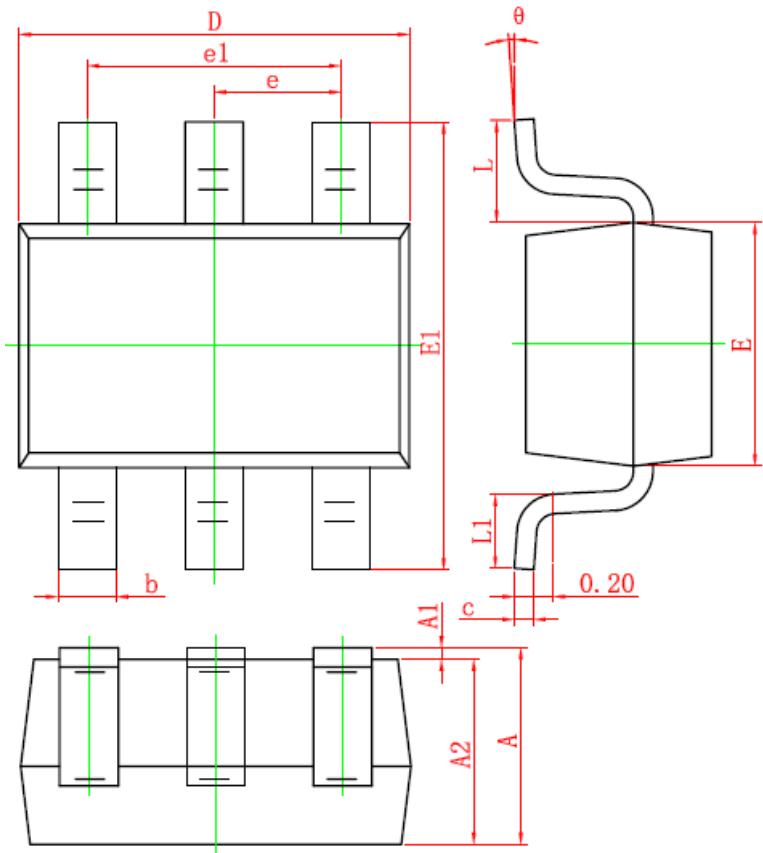
Forward Transfer Admittance vs Drain Current



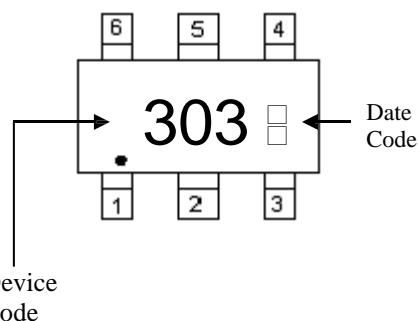
Transient Thermal Response Curves



## SOT-363 Dimension



Marking:



6-Lead SOT-363 Plastic  
Surface Mounted Package  
Code: S6R

Style:

- Pin 1. Source1 (S1)
- Pin 2. Gate1 (G1)
- Pin 3. Drain2 (D2)
- Pin 4. Source2 (S2)
- Pin 5. Gate2 (G2)
- Pin 6. Drain1 (D1)

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					